

Ordering Information

Part Number	Marking	Package	Packing Method
FJP5554TU	J5554	TO-220	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Units
BV _{CBO}	Collector-Base Voltage	1050	V
BV _{CEO}	Collector-Emitter Voltage	400	V
BV _{EBO}	Emitter-Base Voltage	15	V
Ι _C	Collector Current (DC)	4	A
I _{CP}	Collector Current (Pulse)	8	A
I _B	Base Current (DC)	2	Α
I _{BP}	Base Current (Pulse)	4	А
Тj	Junction Temperature	150	°C
T _{STG}	Storage Junction Temperature Range	- 55 to +150	°C

Thermal Characteristics

Values are at $T_{A} = 25^{\circ}$ C unless otherwise noted

Symbol	Parameter	Value	Units	
PD	Total Device Dissipation	T _C = 25°C	70	W
R _{θjc} ⁽¹⁾	Thermal Resistance, Junction to Case		1.78	°C/W

Note:

1. $R_{\theta jc}$ test fixture under infinite cooling condition.

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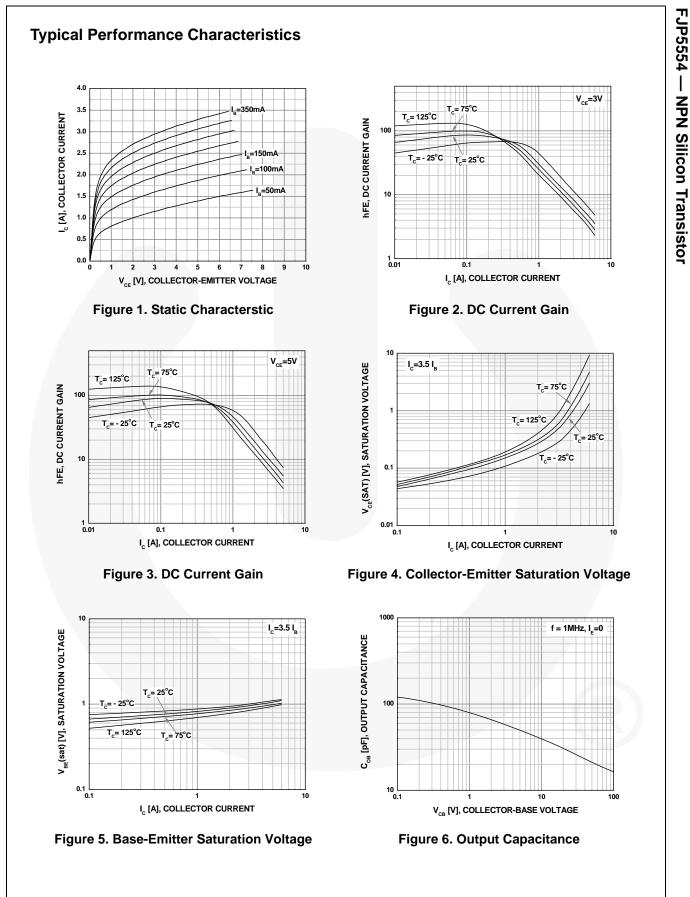
Electrical Characteristics⁽²⁾

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 500 \ \mu A, \ I_{E} = 0$	1050			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 5 \text{ mA}, I_{\rm B} = 0$	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 1 {\rm mA}, I_{\rm C} = 0$	15		23	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 1050 \text{ V}, I_E = 0$			1	mA
I _{CEO}	Collector Cut-Off Current	$V_{CB} = 400 \text{ V}, I_B = 0$			250	μΑ
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 15 \text{ V}, \text{ I}_{C} = 0$			1	mA
h _{FE}	DC Current Gain	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 0.1 \text{ A}$	45		100	
		$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 0.8 \text{ A}$	20		50	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 0.2 A			0.5	V
		I _C = 3.5 A, I _B = 1.0 A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3.5 A, I _B = 1.0 A			1.5	V
t _{ON}	Turn-On Time	V _{CC} =125 V, I _C =0.5 A,			1.0	μs
t _{STG}	Storage Time	$I_{B1} = 45 \text{ mA}, I_{B2} = 0.5 \text{ A},$			1.2	μs
t _F	Fall Time	$R_L = 250 \Omega$			0.3	μs
EAS	Avalanche Energy	L = 2 mH	6			mJ

Note:

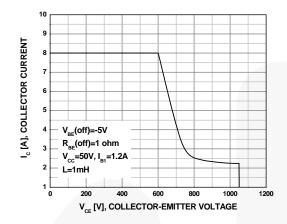
2. Pulse test: pulse width \leq 300 $\mu s,$ duty cycle \leq 2%.



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Typical Performance Characteristics (Continued)



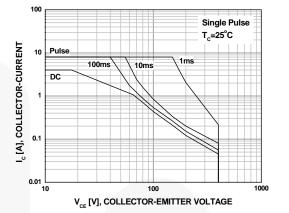


Figure 7. Reverse Biased Safe Operating Area



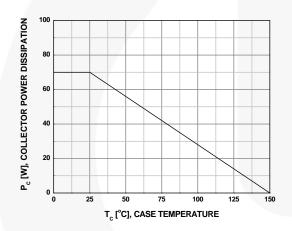
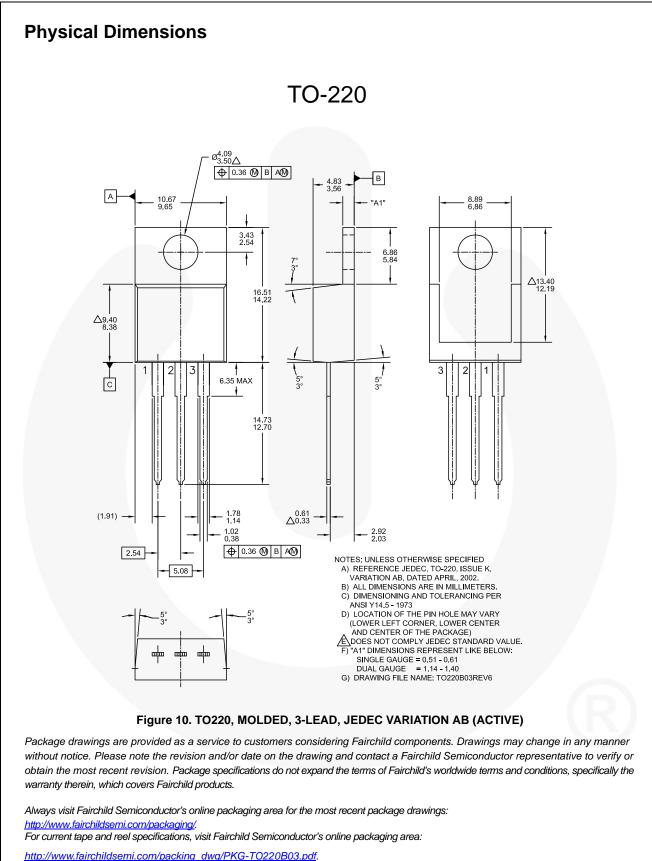


Figure 9. Power Derating Curve



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